Begin	End	Duration	Title	Speaker	Affiliation
9:00	9:05	0:05	**Opening**		
9:05	9:05	0:00	***Session 1***		
9:05	9:40	0:35	**Invited 1 : Embedded Flash Technologies: Enabler for Automotive µCs & Smartcards**	**Robert Strenz**	**Infineon**
9:40	10:00	0:20	Talk 1 : Split-gate charge trap memories: impact of scaling on performances and consumption for low-power embedded applications	Lia Masoero	Leti
10:00	10:20	0:20	Talk 2 : Ab initio simulation applied to innovative memory devices	Philippe Blaise	Leti
10:20	10:55	0:35	**Invited 2 : Embedded non volatile memories for consumer applications: status and perspectives**	**Paola Zuliani**	**ST**
10:55	11:15	0:20	Break		
11:15	11:15	0:00	***Session 2***		
11:15	11:50	0:35	**Invited 3 : Phase-change memories for energy-efficient data-centric IT applications**	**Agostino Pirovano**	**Micron**
11:50	12:10	0:20	Talk 3 : Phase change materials engineering for reset current reduction.	Véronique Sousa	Leti
12:10	12:30	0:20	Talk 4 : Study of GST nanosized clusters	Giada Ghezzi	Leti
12:30	12:50	0:20	Talk 5 : Magnetic memory for hybrid CMOS electronics	Ricardo Sousa	INAC/Spintec
12:50	14:20	1:30	Lunch		
14:20	14:20	0:00	***Session 3***		
14:20	14:55	0:35	**Invited 4 : Phase Change Memory: Replacement or Transformational**	**Hsiang-Lan Lung**	**Macronix**
14:55	15:15	0:20	Talk 6 : Resistive switching concept: a new design paradigm	Jean-Michel Portal	IM2NP
15:15	15:35	0:20	Talk 7 : Using OxRAM for saving power in FPGA architecture: what can we expect?	Fabien Clermidy	Leti
15:35	15:55	0:20	Talk 8 : PCM for Neuromorphic applications	Manan Suri	Leti
15:55	16:15	0:20	Talk 9 : Experimental investigation and empirical modeling of the set and reset kinetics of Ag-GeS2 Conductive Bridging Memories	Elisa Vianello	Leti
16:15	16:35	0:20	Break		
16:35	16:35	0:00	***Session 4***		
16:35	17:10	0:35	**Invited 5 : Resistive Memory Technology for High Density Memory Applications.**	**Sunjung Kim**	**Samsung**
17:10	17:30	0:20	Talk 10 : Characterization and Modelling of Electrode Impact in HfO2-based RRAM	Carlo Cagli	Leti
17:30	17:50	0:20	Talk 11 : In-operando HAXPES as a non-destructive technique for investigating the resistive switching phenomenon	Thomas Bertaud	IHP
17:50	18:10	0:20	Talk 12 : Study of ReRAM based on TiN/ TaxOy /TiN integrated into a 65nm advanced CMOS technology	Thérèse Diokh	ST
18:10	18:15	0:05	**Conclusions**		